

6. (Original) The method of claim 1, which further comprises producing a bonding layer on at least one of the bonding face of the donor wafer or on the support, or on both, to improve bonding strength therebetween.

7. (Original) The method of claim 6, wherein that the bonding layer is configured to form a buried insulator in the product substrate.

8. (Original) The method of claim 1, wherein transfer layer comprises a Group III-V semiconductor.

9. (Cancelled)

10. (Original) The method of claim ~~9~~¹, wherein the transfer layer is made of indium phosphide.

11. (Original) The method of claim 10, wherein the foreign atomic species comprises at least one of iron or rhodium.

12. (Original) The method of claim 10, wherein the foreign atomic species comprises a shallow acceptor and a shallow donor.

13. (Original) The method of claim 1, wherein the implanted atomic species that forms the weakened zone comprises at least one of hydrogen ions and rare gas ions.

14. (Original) The method of claim 1, wherein the support material is mechanically stronger than the transfer layer.

15. (Original) The method of claim 1, which further comprises epitaxially growing an epitaxial layer on the transfer layer of the substrate after the detaching.

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